

## PATENT APPLICATION

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re A	pplication of:		#11/F/D 7/16/2,						
	Akihiro NITAYAMA et al.	) Group Art No. 2814	Surler						
Serial 1	No: 09/660,390	Examiner: H. Weiss							
Filed:	September 12, 2000	Docket No. 000629.0000	2 <del>/</del>						
For:	DYNAMIC SEMICONDUCTOR MEMORY DEVICE HAVING A TRENCH CAPACITOR AND METHOD OF MANUFACTURING THE SAME SUBMISSION OF CORRECTED FORMAL DRAWINGS								
SUBMISSION OF CORRECTED FORMAL DRAWINGS									

Assistant Commissioner for Patents Washington, D.C. 20231

Sir:

In accordance with the final Office Action dated May 1, 2002, submitted herewith are fifty-four (54) sheets of formal corrected drawings (Figs. 1a-33). These drawings include the changes to Figs. 1a, 1b, 2a and 2b, as set forth in the proposed drawing correction filed March 18, 2002, which were approved in the final Action.

Respectfully submitted,

#42,402

Joseph M. Potenza Registration No. 28,175

BANNER & WITCOFF, LTD. 1001 G Street, N.W., 11<sup>th</sup> Floor Washington, D.C. 20001 (202) 508-9100

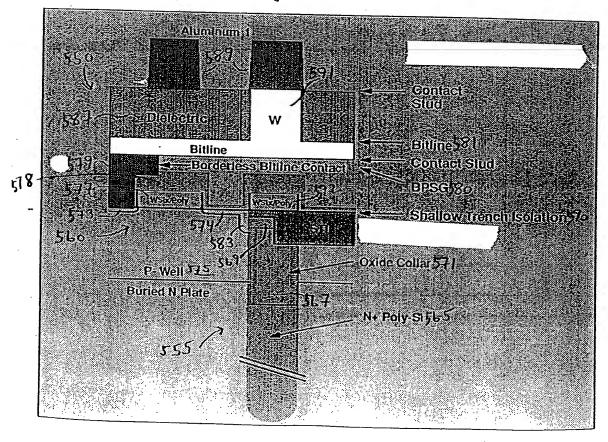
Date: July 1, 2002

Bit Line Active Area (AA) Trench
579

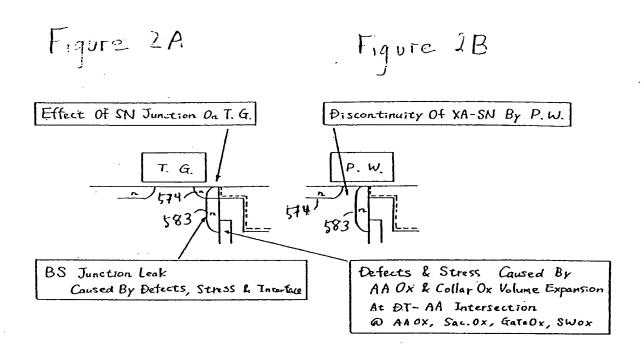
A

Wordlines
Prior Art

Figure 1B



**Prior Art** 



**Prior Art** 

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Figure 3

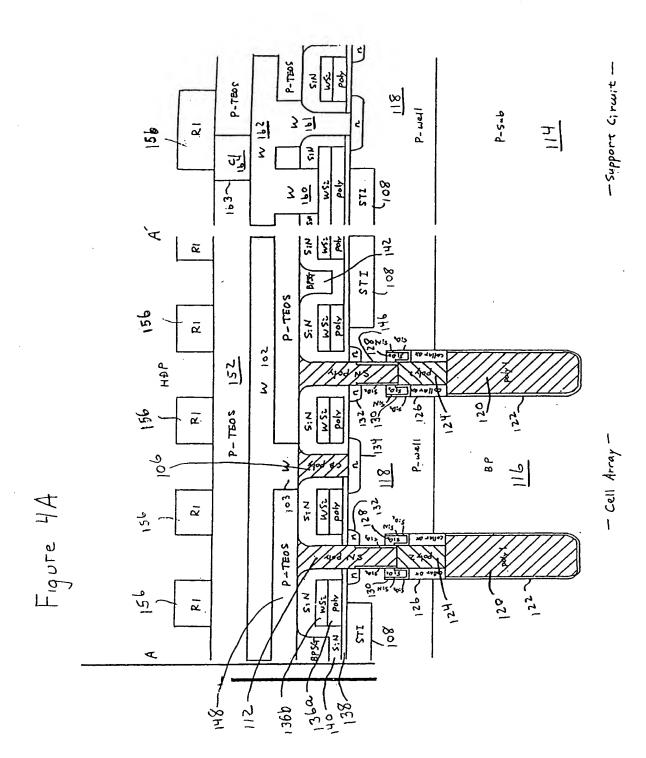
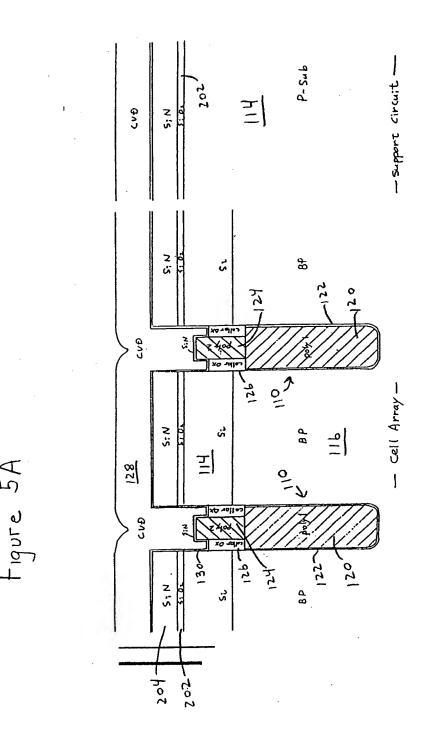
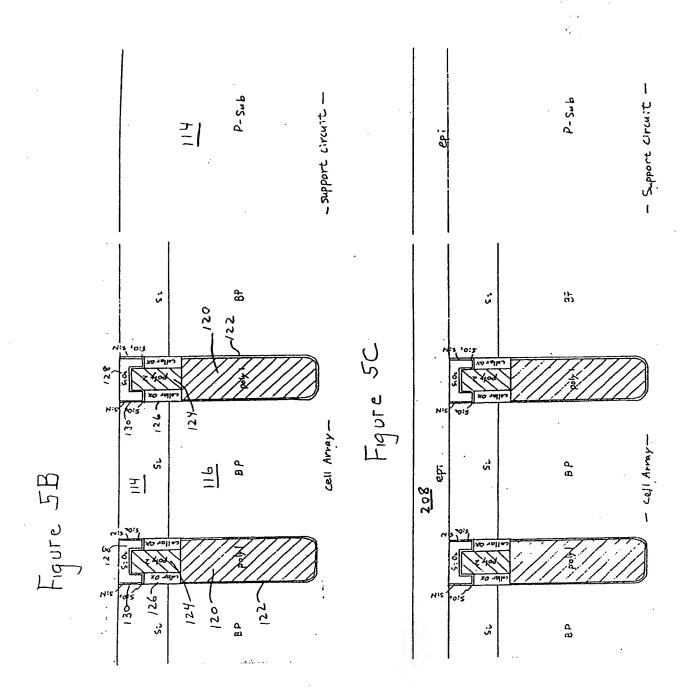


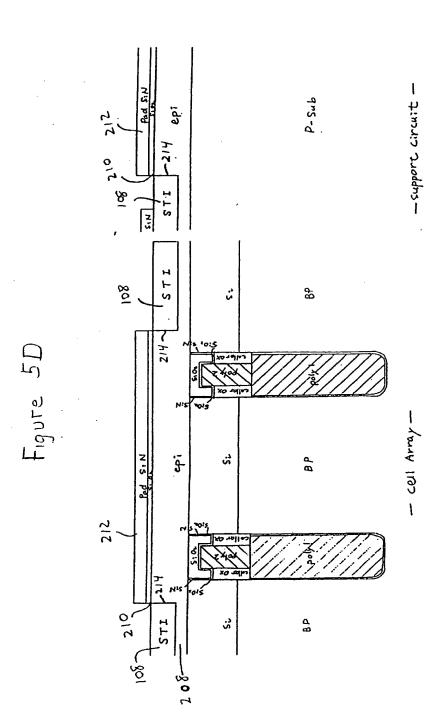
Figure 4B

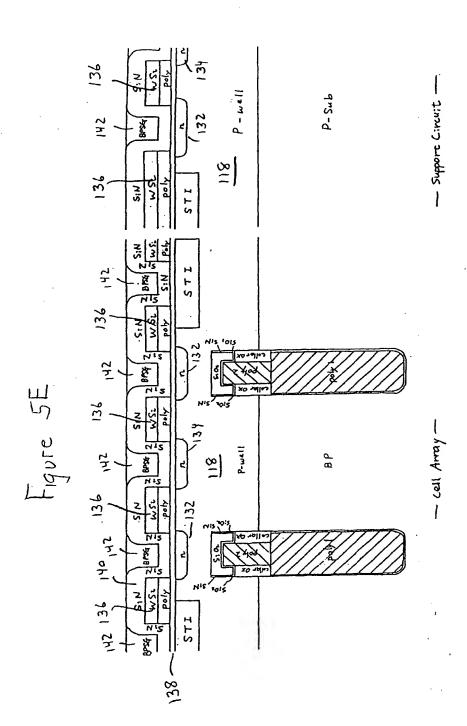
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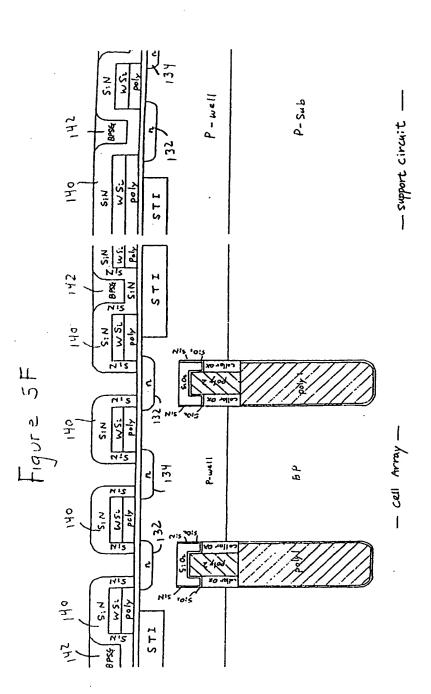
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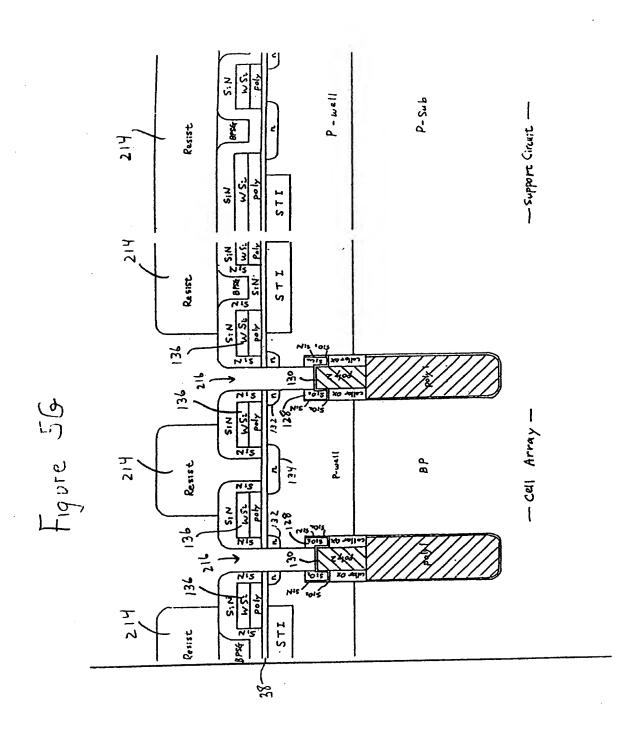












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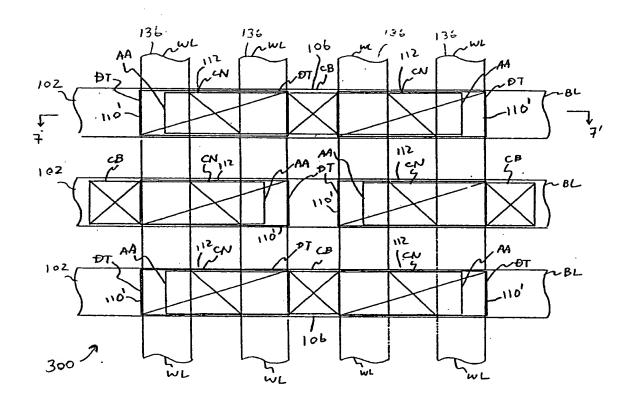
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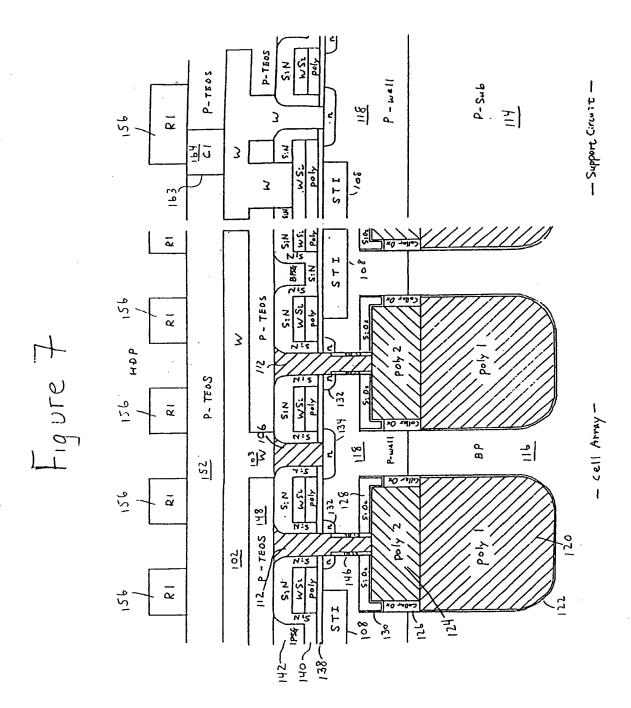
P-TEOS -Surport armit -P-well 29/3 Nis Z Bras Figure SI P - TEOS 3 - cell Army -901 Pewall ВР 嘭 022 P - TEOS 701 STI

-cell Array -

-Support Circuit -

## Figure 6





## Figure 8

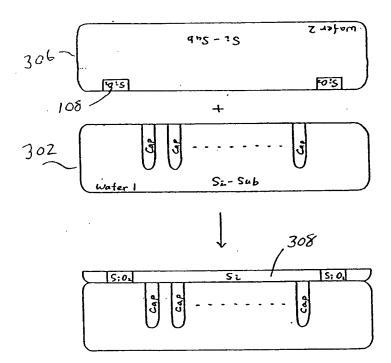
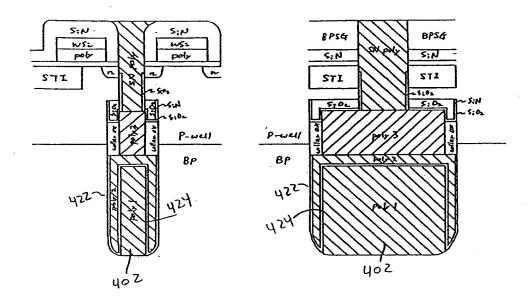


Figure 9A

Figure 9B



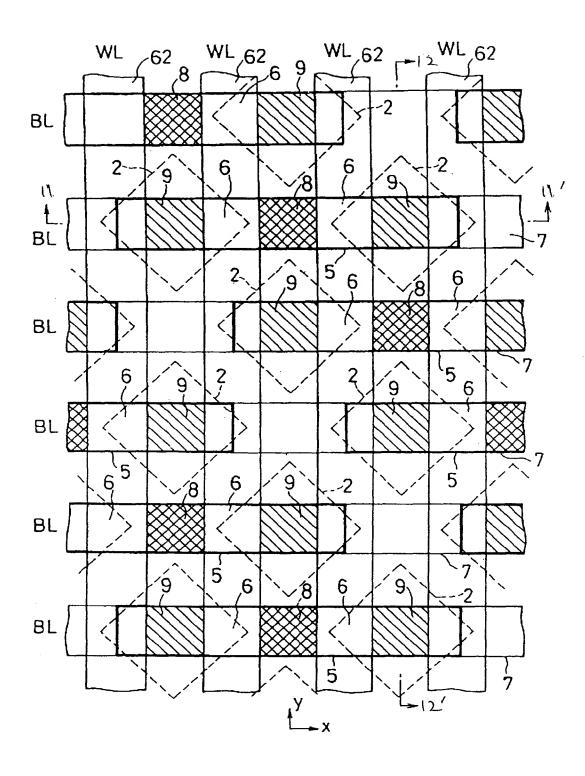


Figure 10

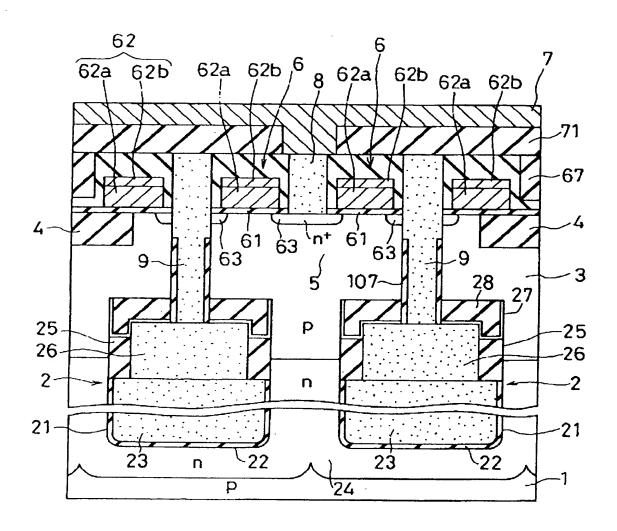


Figure 11

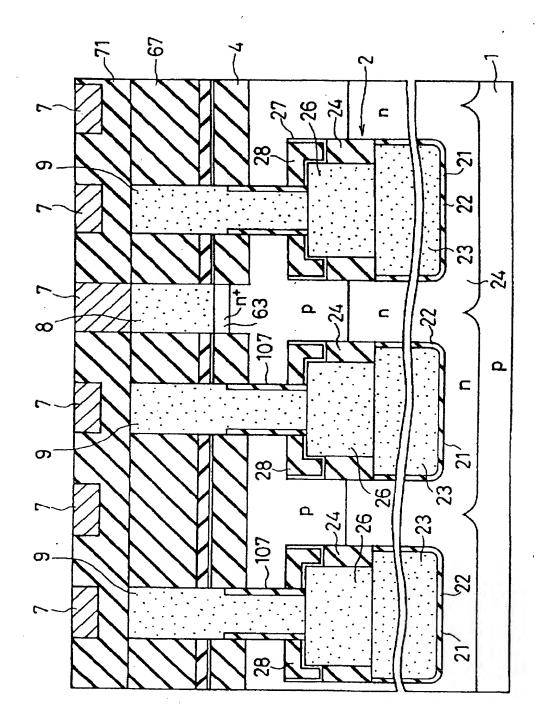
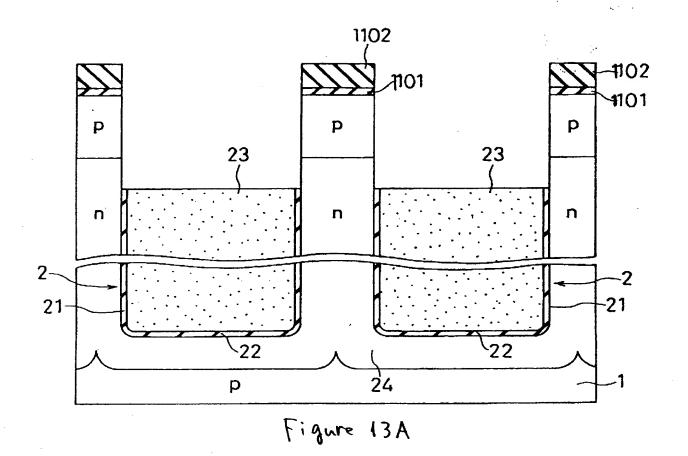


Figure 12



25 +102 26 26 1101 p p p n n n 2--2 23 21--21 22 24 p Figure 13 B

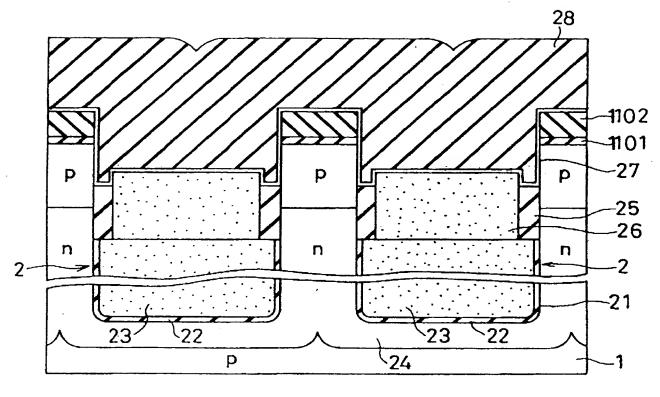


Figure 13C

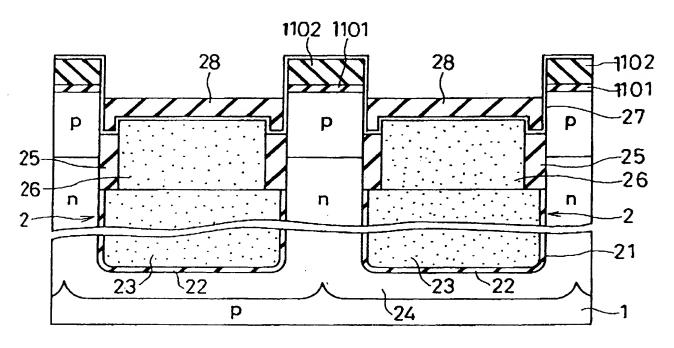


Figure 13D

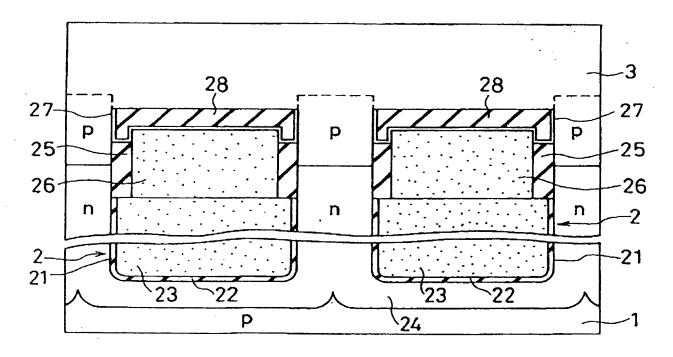


Figure 13E

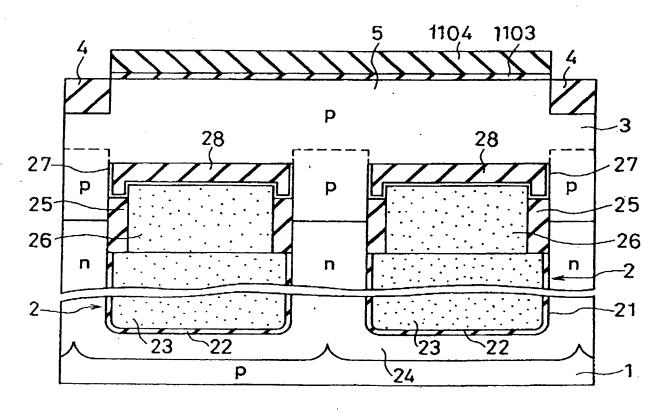
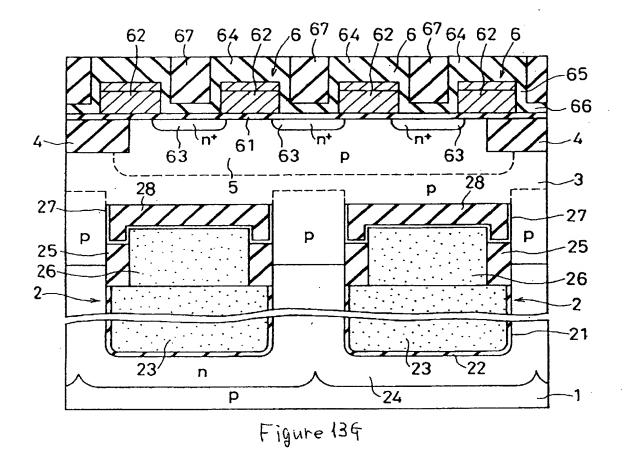
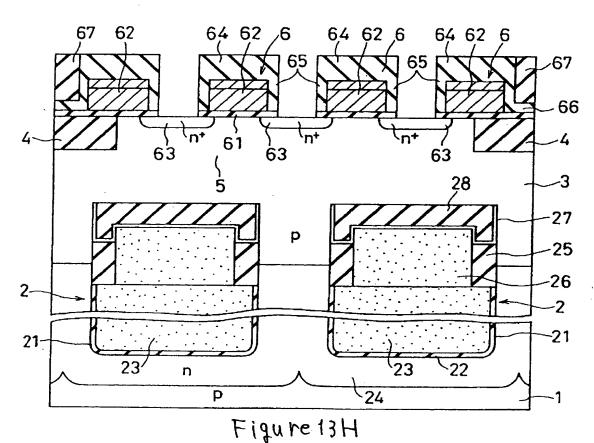
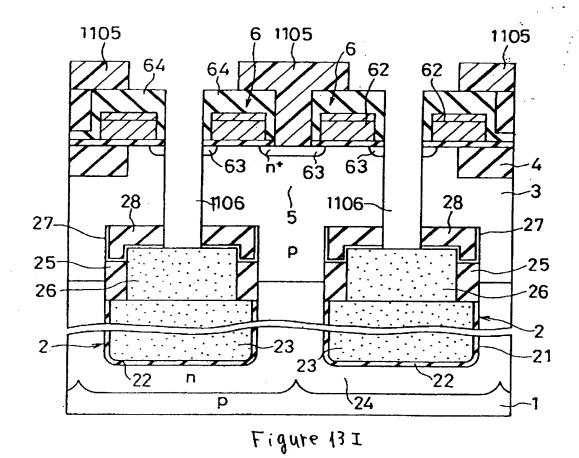


Figure 13F







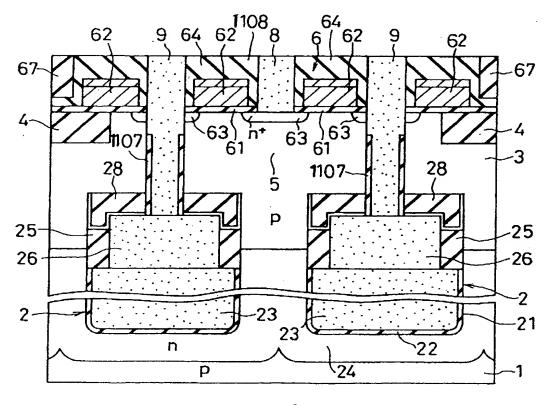


Figure 13J

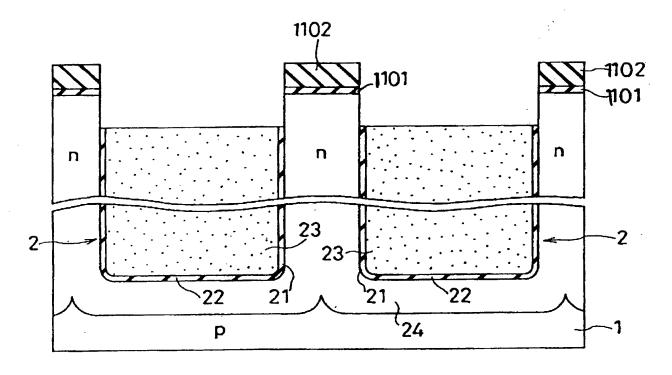


Figure 14A

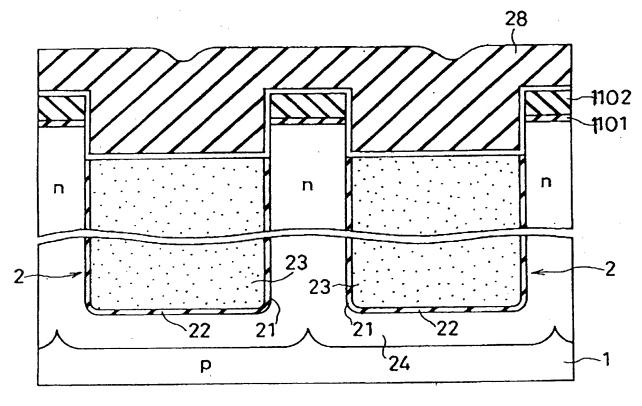
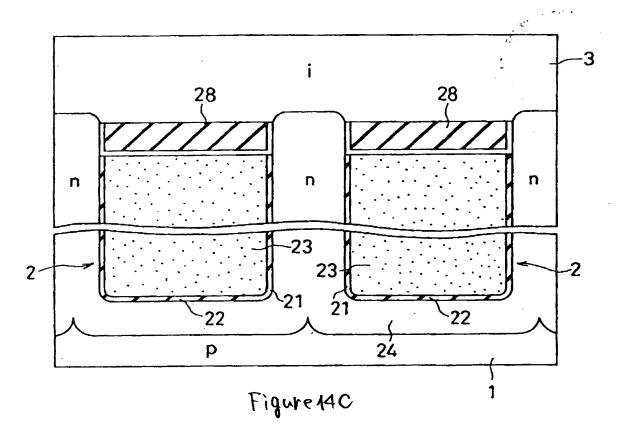


Figure 14B



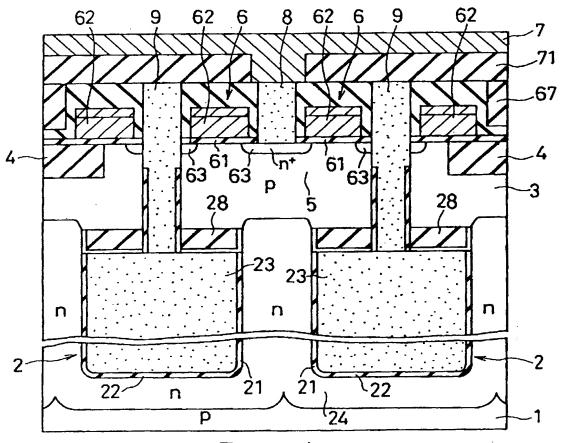


Figure 14D

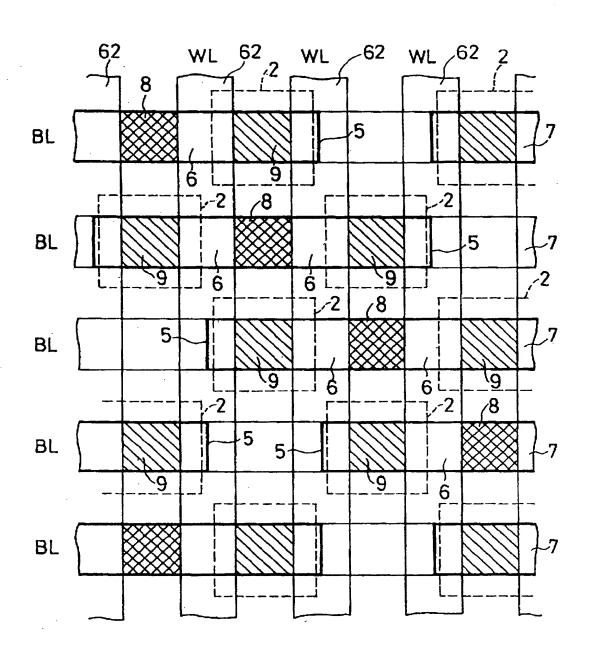
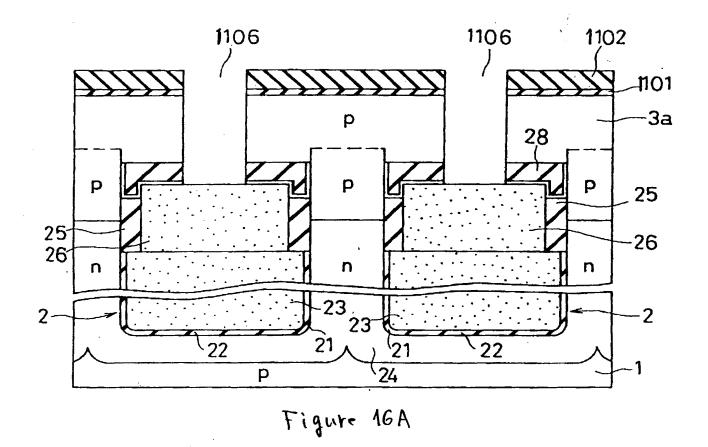


Figure 15



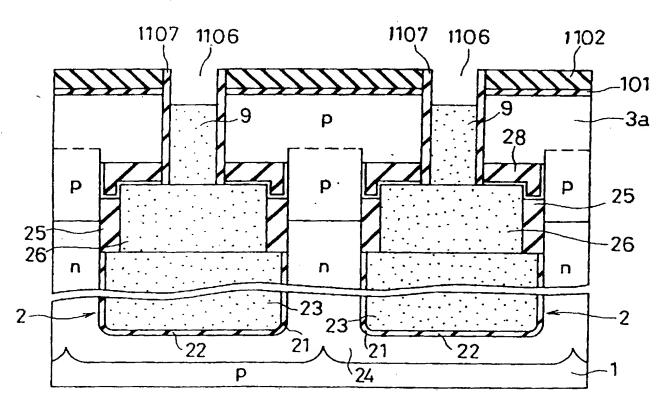


Figure 16B

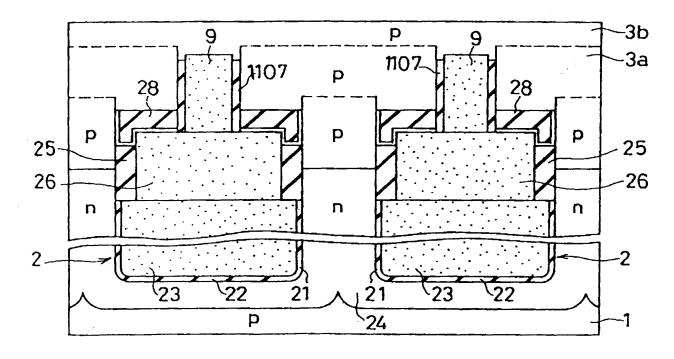


Figure 160

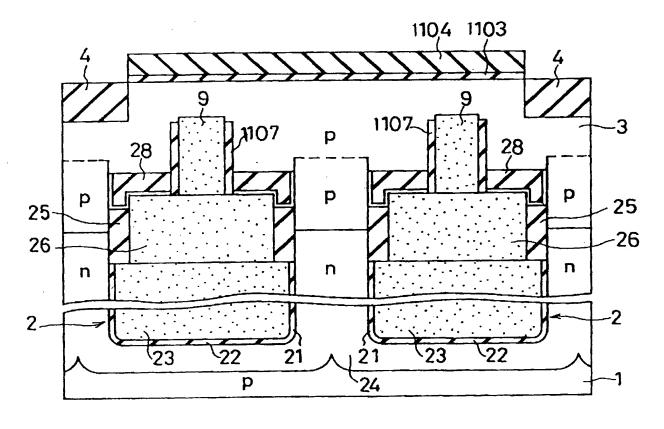


Figure 16D

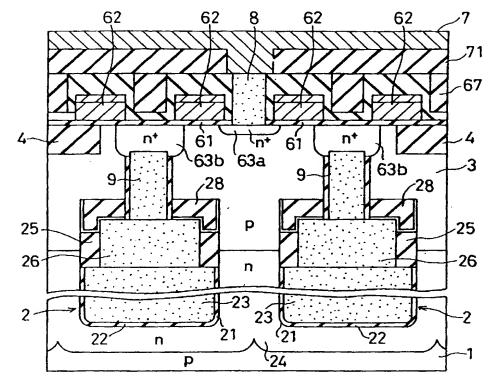


Figure 16E

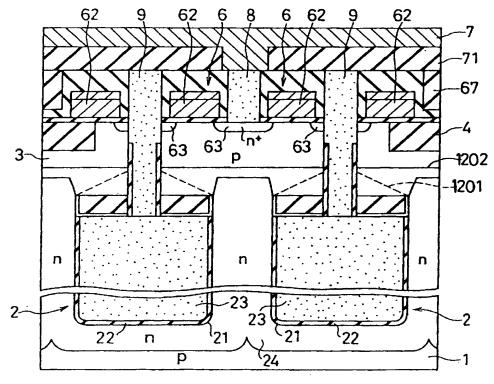


Figure 17

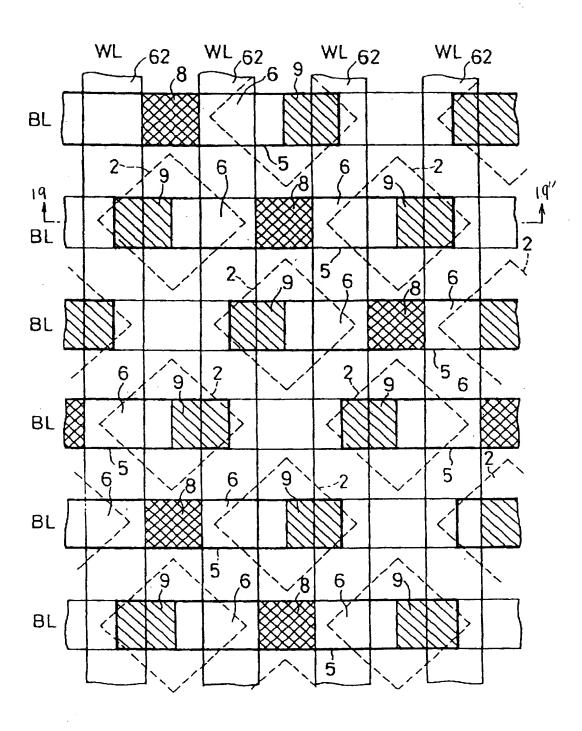


Figure 18

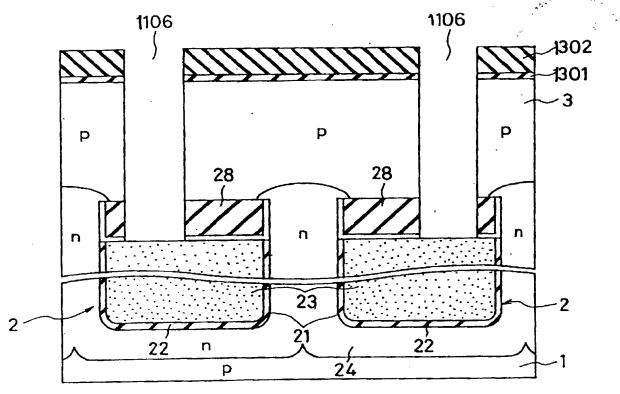


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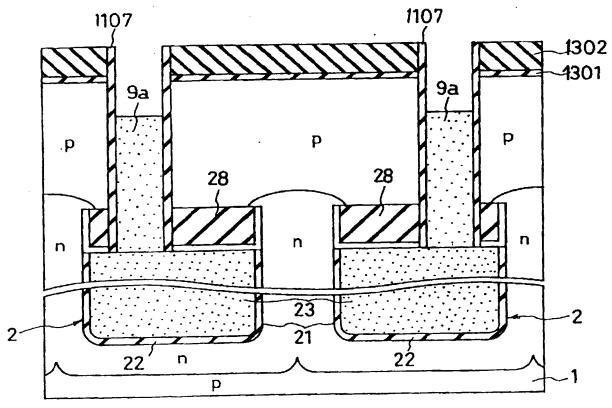


Figure 19B

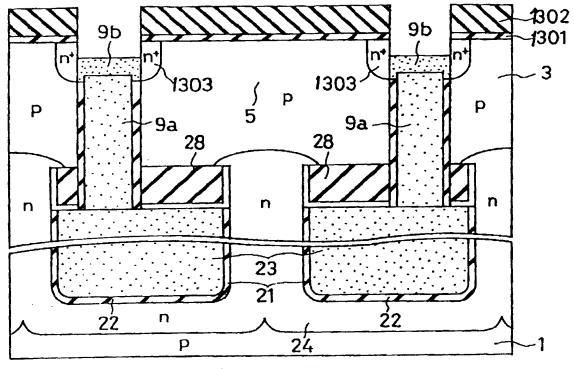


Figure 190

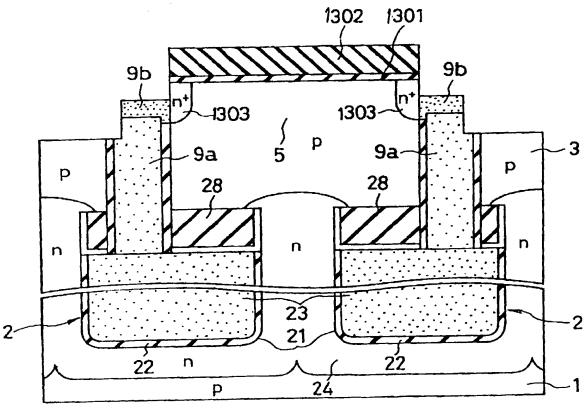


Figure 19D

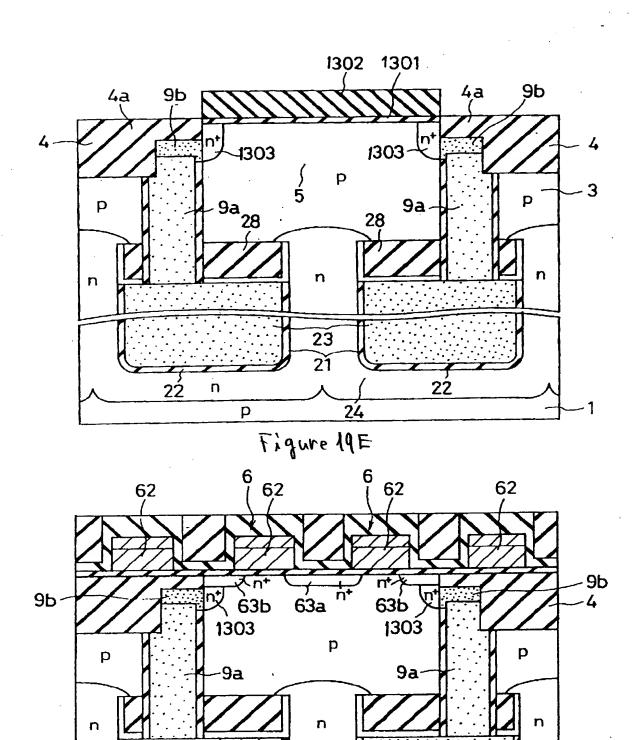


Figure 19F

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<u>22</u>

- 2

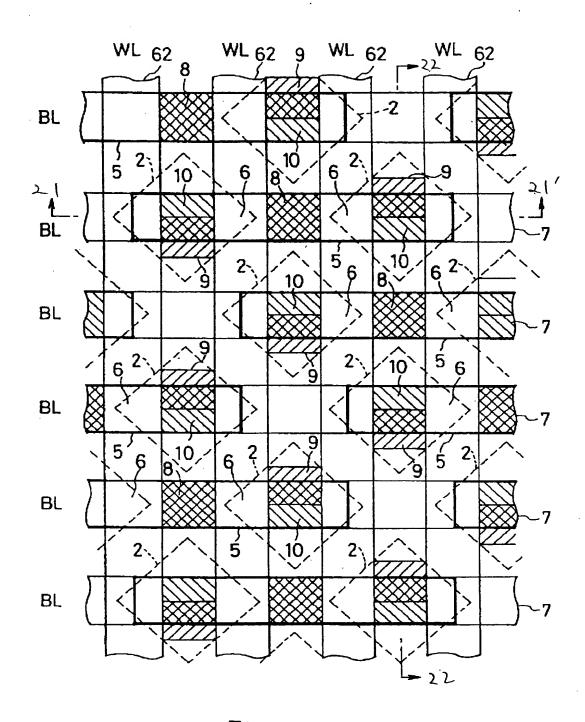


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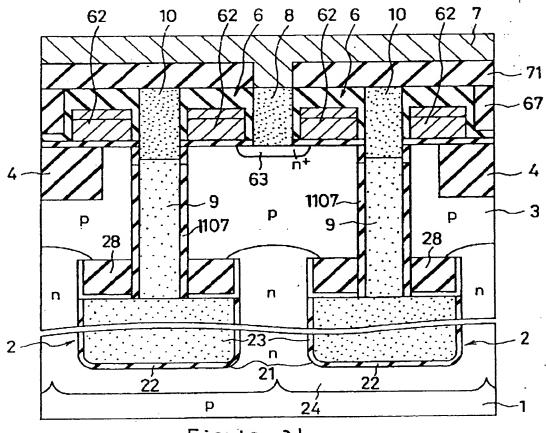


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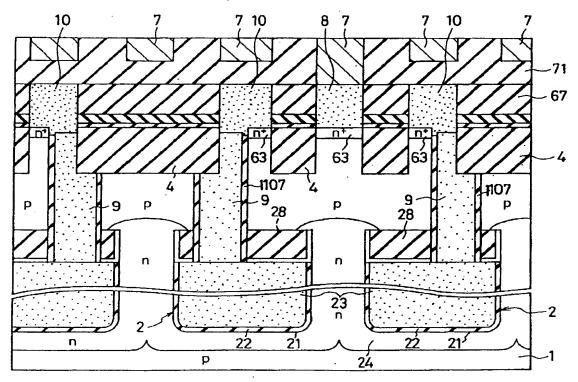
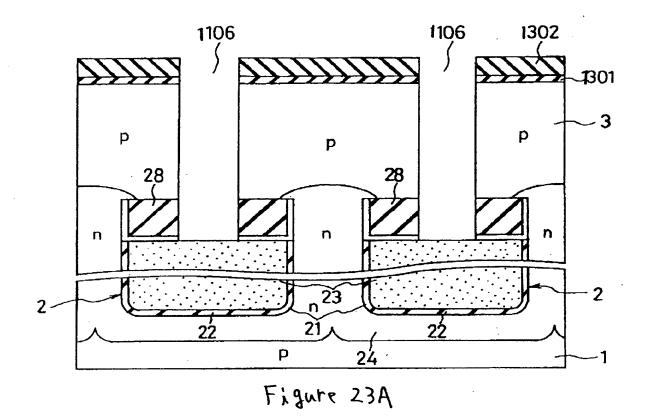
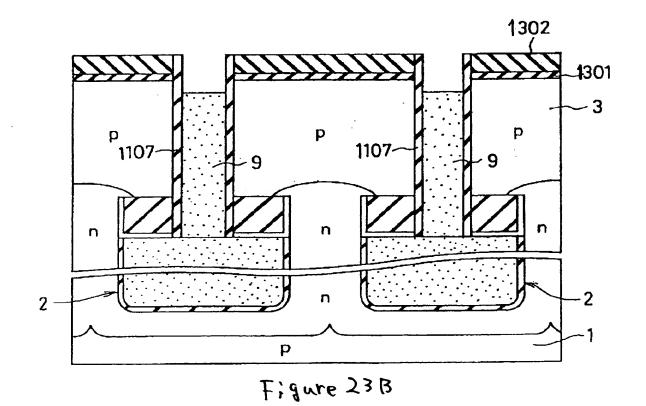
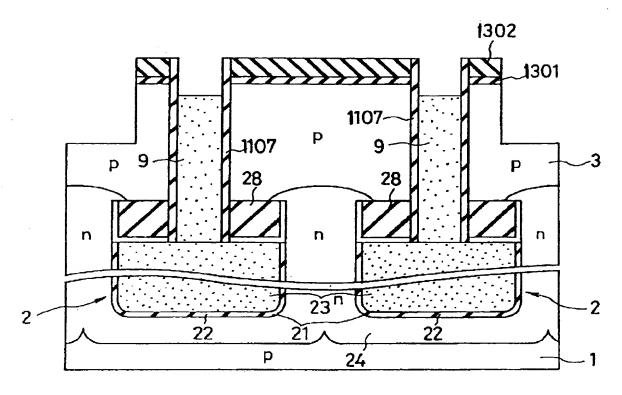


Figure 22







Flaure 23C

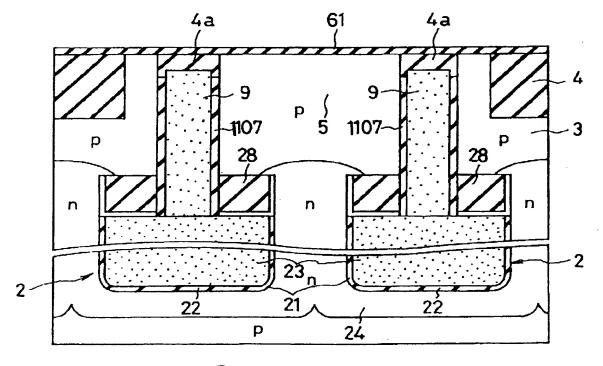
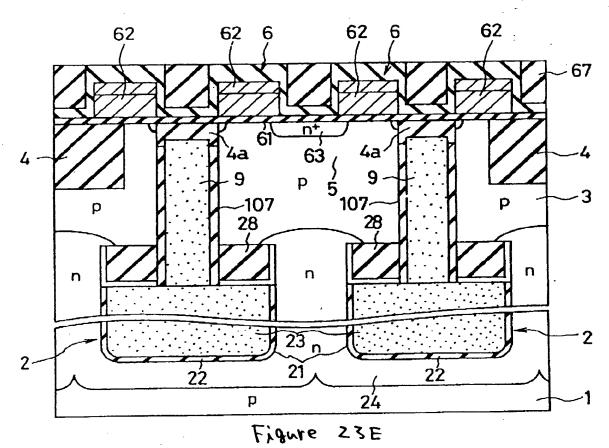


Figure 23D



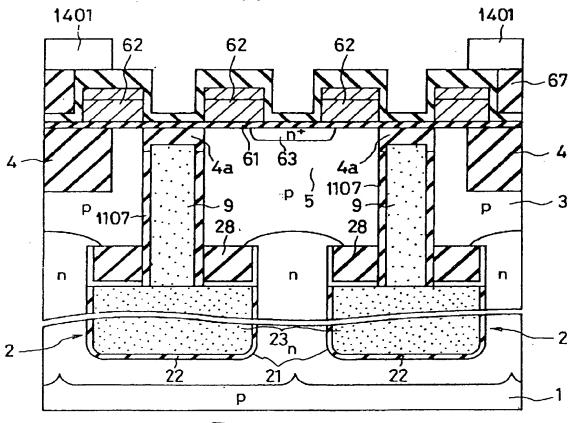
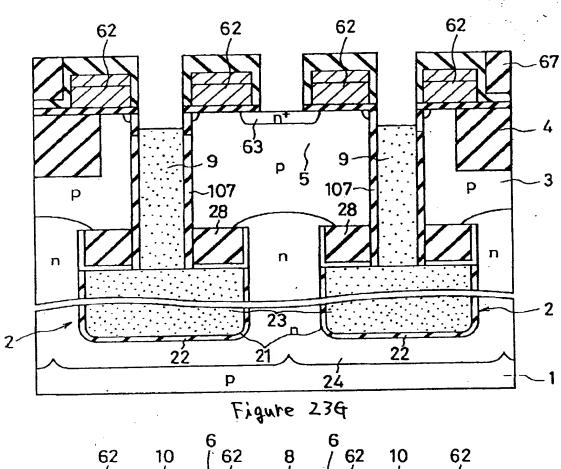
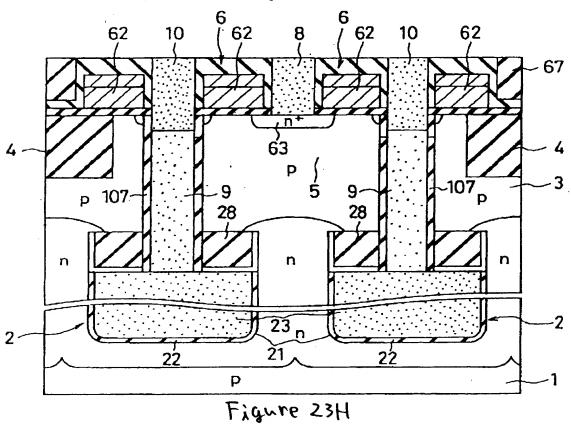


Figure 23F





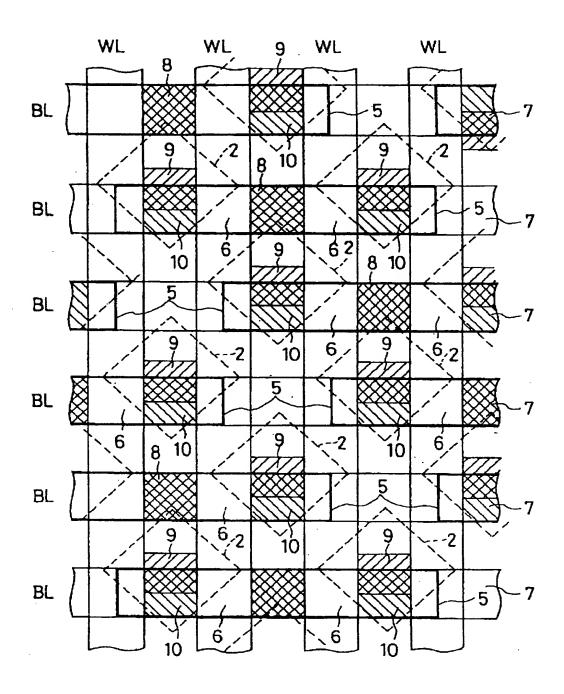


Figure 24

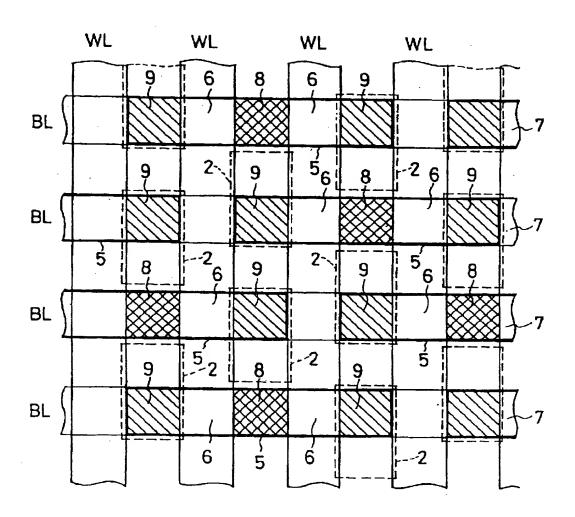
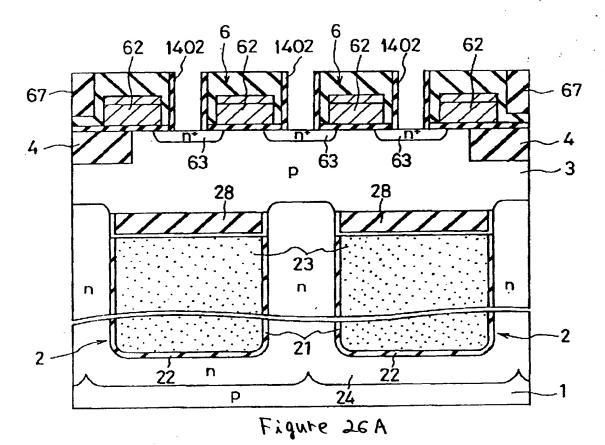


Figure 25



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Figure 26B

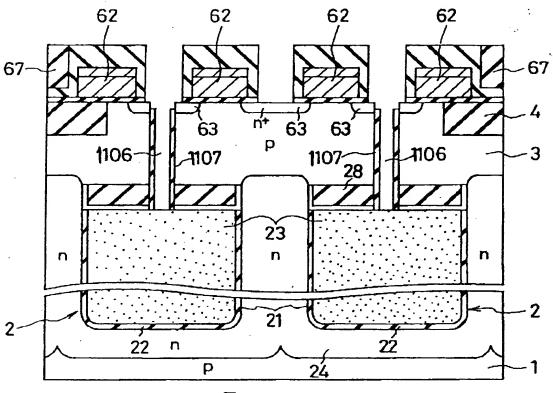


Figure 26C

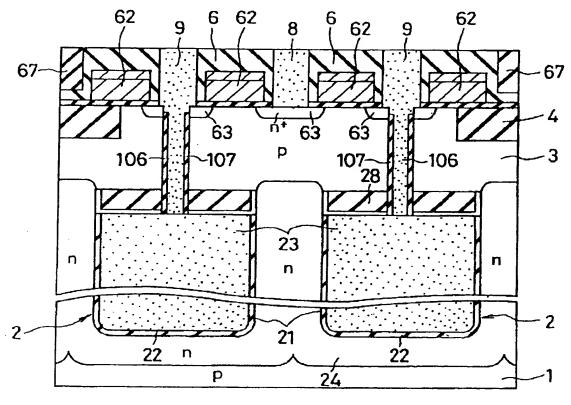


Figure 26D

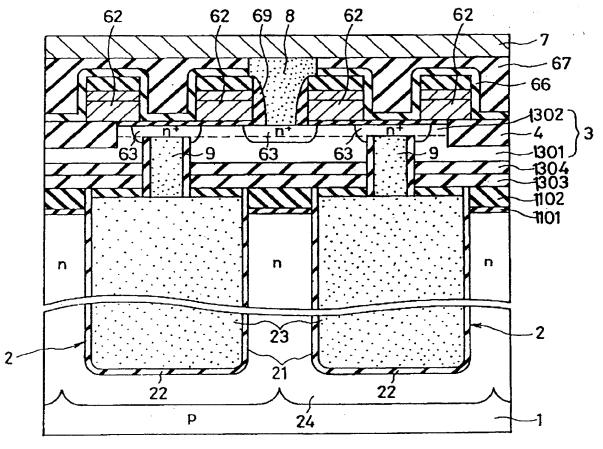


Figure 27

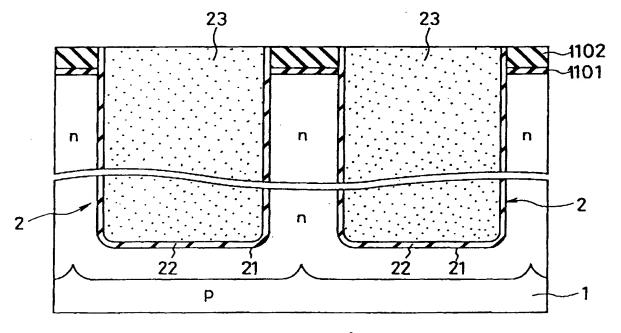


Figure 28A

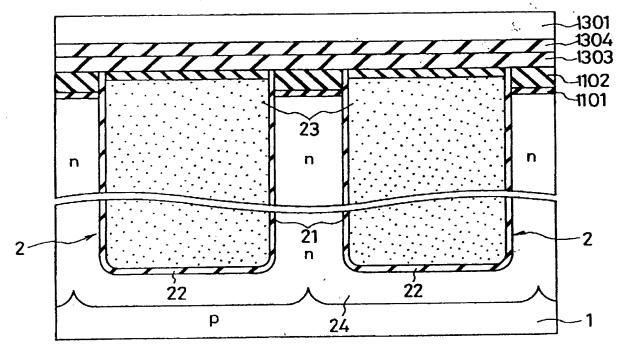


Figure 28B

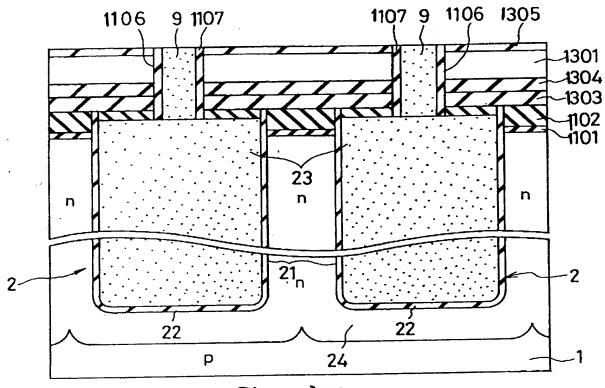


Figure 28C

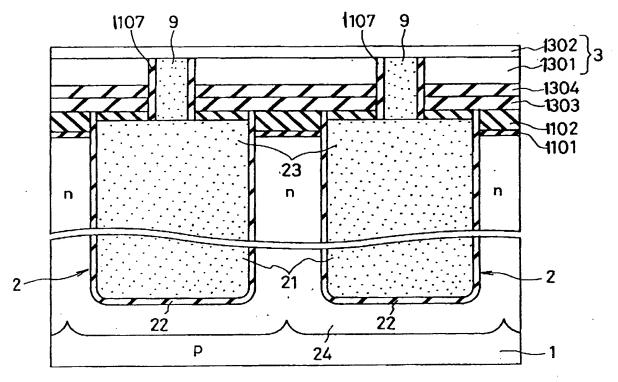


Figure 280

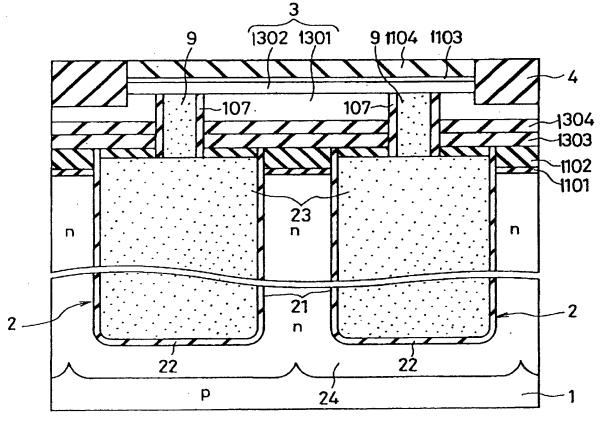


Figure 28E

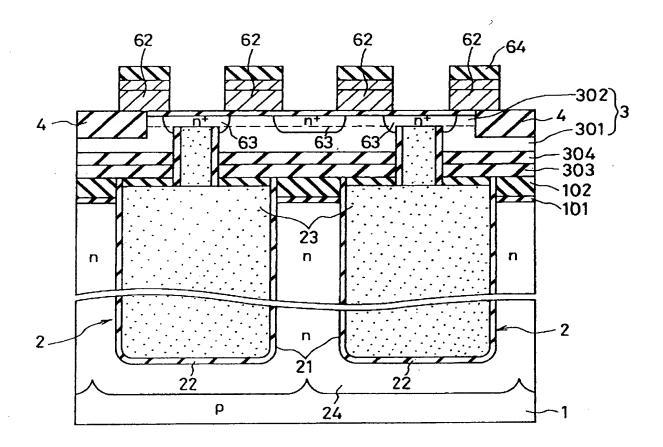


Figure 18F

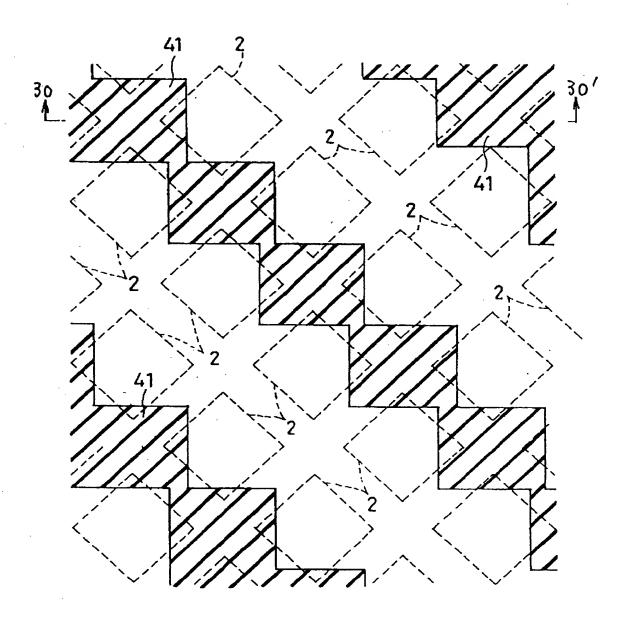


Figure 29

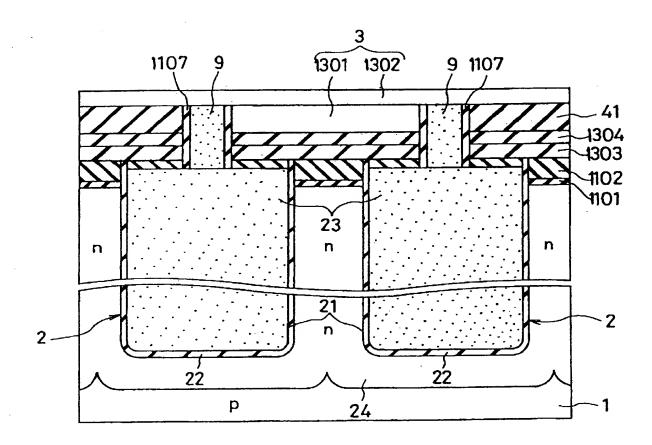


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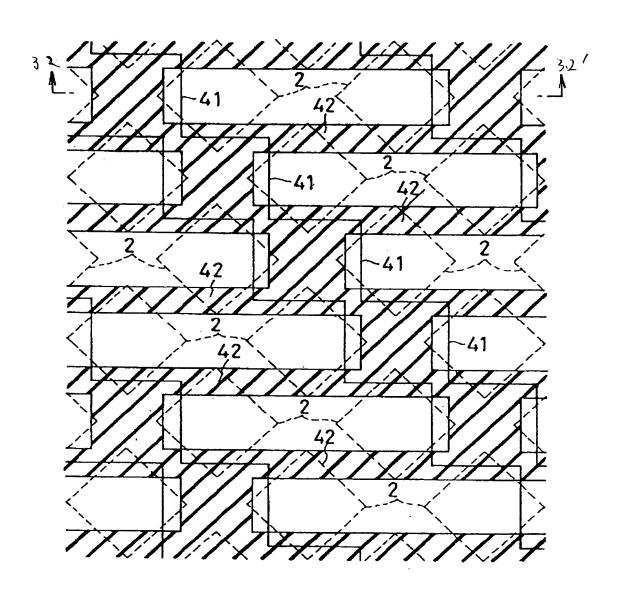


Figure 31

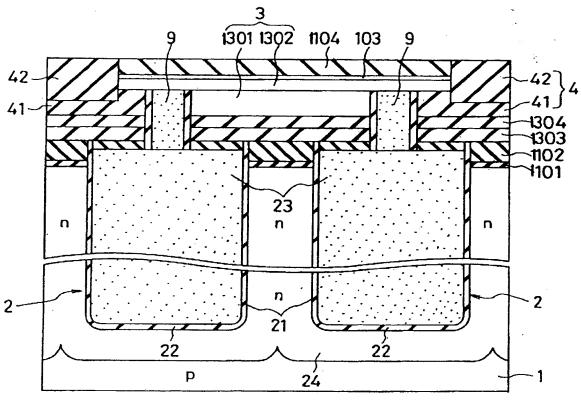


Figure 32

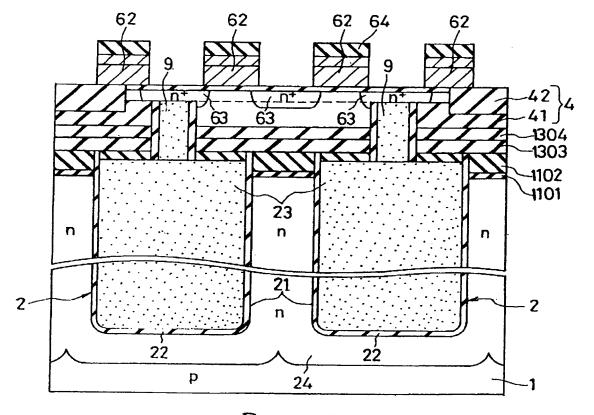


Figure 33